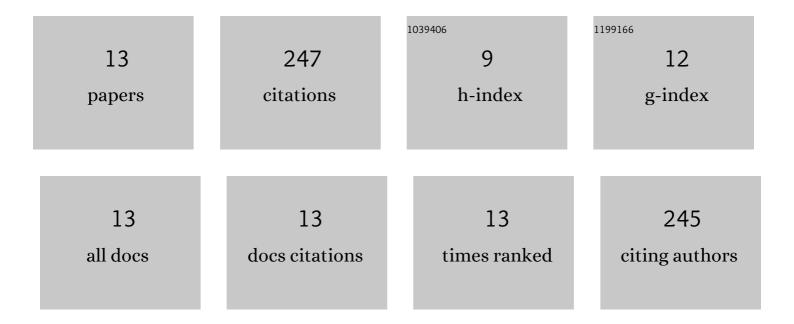
Christian J Zollner

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Size dependent characteristics of AlGaN-based deep ultraviolet micro-light-emitting-diodes. Applied Physics Express, 2022, 15, 064003.	1.1	7
2	Effect of nucleation layer thickness on reducing dislocation density in AlN layer for AlGaN-based UVC LED. Microelectronics International, 2021, 38, 113-118.	0.4	1
3	Highly Conductive n-Al0.65Ga0.35N Grown by MOCVD Using Low V/III Ratio. Crystals, 2021, 11, 1006.	1.0	12
4	Growth of highly conductive Al-rich AlGaN:Si with low group-III vacancy concentration. AIP Advances, 2021, 11, .	0.6	13
5	Germicidal ultraviolet LEDs: a review of applications and semiconductor technologies. Semiconductor Science and Technology, 2021, 36, 123001.	1.0	32
6	High conductivity n-Al _{0.6} Ga _{0.4} N by ammonia-assisted molecular beam epitaxy for buried tunnel junctions in UV emitters. Optics Express, 2021, 29, 40781.	1.7	5
7	AlGaN Deep-Ultraviolet Light-Emitting Diodes Grown on SiC Substrates. ACS Photonics, 2020, 7, 554-561.	3.2	59
8	Superlattice hole injection layers for UV LEDs grown on SiC. Optical Materials Express, 2020, 10, 2171.	1.6	11
9	Reduced dislocation density and residual tension in AlN grown on SiC by metalorganic chemical vapor deposition. Applied Physics Letters, 2019, 115, .	1.5	29
10	Fabrication technology for high light-extraction ultraviolet thin-film flip-chip (UV TFFC) LEDs grown on SiC. Semiconductor Science and Technology, 2019, 34, 035007.	1.0	33
11	Impact of roughening density on the light extraction efficiency of thin-film flip-chip ultraviolet LEDs grown on SiC. Optics Express, 2019, 27, A1074.	1.7	17
12	Low threading dislocation density aluminum nitride on silicon carbide through the use of reduced temperature interlayers. Journal of Crystal Growth, 2018, 483, 134-139.	0.7	20
13	Developments in AlGaN and UV-C LEDs grown on SiC. , 2018, , .		8